

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	3	("4142926").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/26 14:43
S2	12667	semiconductor with lithography	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 14:46
S3	24	S2 and (thin film stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:47
S4	1543042	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 14:46
S5	43735	S4 and lithography	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 14:46
S6	93	S5 and (thin film stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:47
S7	0	S5 and ((thin film stack) with polysilicon with oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:48
S8	0	S5 and ((thin film stack) same polysilicon same oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:49
S9	10	S5 and ((thin film stack) and polysilicon and oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:57

S10	4	S9 and ((anti reflectie) or ARC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:58
S11	4	S10 and \$5mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:58
S12	71	S4 and ((thin film stack) and polysilicon and oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:57
S13	15	S12 and ((anti reflectie) or ARC) and \$5mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 15:00
S14	15	S13 and etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:59
S15	4	S14 and (((anti reflectie) or ARC) with pattern)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:02
S16	0	S4 and (((anti reflectie) or ARC) with pattern with hardmask) and ((thin film stack) with hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:05
S17	0	S4 and (((anti reflectie) or ARC) same pattern same hardmask) and ((thin film stack) with hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:06
S18	0	S4 and (((anti reflectie) or ARC) same pattern same hardmask) and ((thin film stack) same hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:08
S19	0	S4 and (((anti reflectie) or ARC) same hardmask) and ((thin film stack) same hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:07

S20	160	S4 and (((anti reflectie) or ARC) same hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:07
S21	130	S4 and (((anti reflectie) or ARC) with hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:07
S22	64	S4 and (((anti reflectie) or ARC) same pattern same hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:08
S23	0	S4 and (((anti reflectie) or ARC) same pattern same hardmask) and (thin film stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:09
S24	445	S4 and (thin film stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:11
S25	0	S4 and ((thin film stack) with hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:11
S26	10	S4 and ((thin film stack) with \$5mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:12